CLAIMS

What is claimed is:

1	1.	A method for forming a channel device comprising the steps of:
2		a) providing at least one active region on a substrate wherein the active
3	region compris	ses a plurality of discontinuous gate structures; and
4		b) providing an ion implantation in the substrate.
1	2.	The method of claim 1 wherein step b) further comprises:
2		b1) masking the plurality of gate structures prior to the ion implantation.
1	3.	The method of claim 2 wherein the active region comprises three gate
2	structures.	
1	4.	The method of claim 3 wherein each of the three gate structures comprises a
2	channel length	of at least $0.13 \mu m$ disposed at least $0.2 \mu m$ apart.
1	5.	The method of claim 1 wherein the ion implantation comprises a lightly doped
2	drain implant.	
1	6.	The method of claim 5 wherein the ion implantation further comprises a halo
2	implant.	

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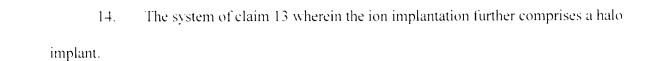
The method of claim 5 wherein the ion implantation further comprises a pocket 7. 1 implant. 2 The method of claim 1 wherein each of the plurality of discontinuous gate 8. 1 structures are connected to a gate voltage source. 2 A system for forming a channel device comprising: 9. means for providing at least one active region on a substrate wherein the active region comprises a plurality of gate structures; and means for providing an ion implantation in the substrate. The system of claim 9 wherein means for providing the ion implantation further 10. 1 comprises: 2 means for masking the plurality of gate structures prior to the ion implantation. 3 The system of claim 10 wherein the active region comprises three gate 11 1 structures. 2 The system of claim 11 wherein each of the three gate structures comprises a 12. 1 channel length of at least $0.13\mu m$ disposed at least $0.2\mu m$ apart. 2 The system of claim 10 wherein the ion implantation comprises a lightly doped

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drain implant.

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- 1 15. The system of claim 13 wherein the ion implantation further comprises a pocket implant.
- 1 16. The system of claim 9 wherein each of the plurality of discontinuous gate structures are connected to a gate voltage source.

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